



Power MOSFET

| PRODUCT SUMMARY | | |
|---------------------------|------------------------|-----|
| V_{DS} (V) | 500 | |
| $R_{DS(on)}$ (Ω) | $V_{GS} = 10\text{ V}$ | 1.5 |
| Q_g (Max.) (nC) | 38 | |
| Q_{gs} (nC) | 5.0 | |
| Q_{gd} (nC) | 22 | |
| Configuration | Single | |

FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available

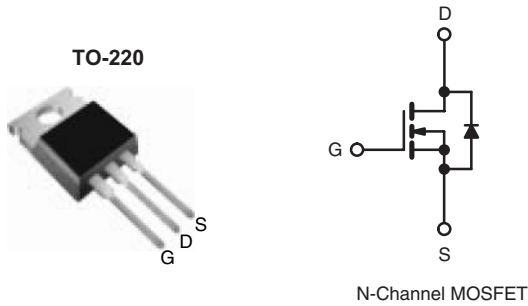


RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



| ORDERING INFORMATION | |
|----------------------|------------|
| Package | TO-220 |
| Lead (Pb)-free | IRF830PbF |
| | SiHF830-E3 |
| SnPb | IRF830 |
| | SiHF830 |

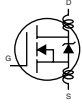

| ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | |
|------------------------------------------------------------------------------------|----------------------------------|----------------|-----------------------------------|---------------------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-Source Voltage | | V_{DS} | 500 | V |
| Gate-Source Voltage | | V_{GS} | ± 20 | |
| Continuous Drain Current | V_{GS} at 10 V | I_D | $T_C = 25\text{ }^\circ\text{C}$ | A |
| | | | $T_C = 100\text{ }^\circ\text{C}$ | |
| Pulsed Drain Current ^a | | I_{DM} | 18 | |
| Linear Derating Factor | | | 0.59 | W/ $^\circ\text{C}$ |
| Single Pulse Avalanche Energy ^b | | E_{AS} | 280 | mJ |
| Repetitive Avalanche Current ^a | | I_{AR} | 4.5 | A |
| Repetitive Avalanche Energy ^a | | E_{AR} | 7.4 | mJ |
| Maximum Power Dissipation | $T_C = 25\text{ }^\circ\text{C}$ | P_D | 74 | W |
| Peak Diode Recovery dV/dt ^c | | dV/dt | 3.5 | V/ns |
| Operating Junction and Storage Temperature Range | | T_J, T_{stg} | - 55 to + 150 | $^\circ\text{C}$ |
| Soldering Recommendations (Peak Temperature) | for 10 s | | 300 ^d | |
| Mounting Torque | 6-32 or M3 screw | | 10 | |
| | | | 1.1 | N · m |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^\circ\text{C}$, $L = 24\text{ mH}$, $R_G = 25\text{ }\Omega$, $I_{AS} = 4.5\text{ A}$ (see fig. 12).
- $I_{SD} \leq 4.5\text{ A}$, $dI/dt \leq 75\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.

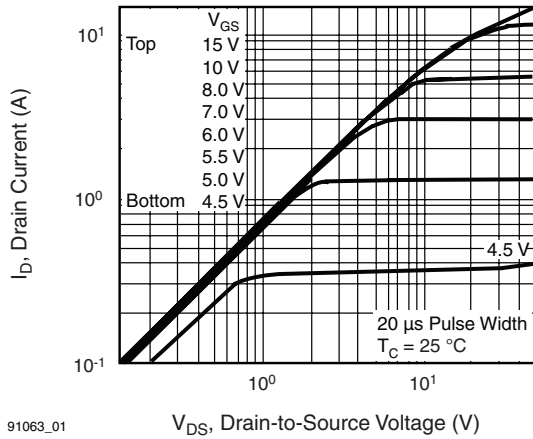
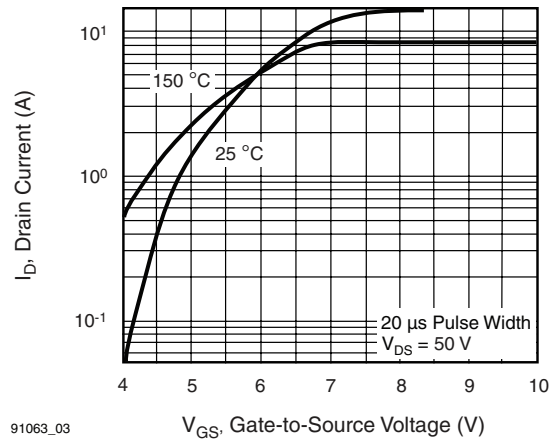
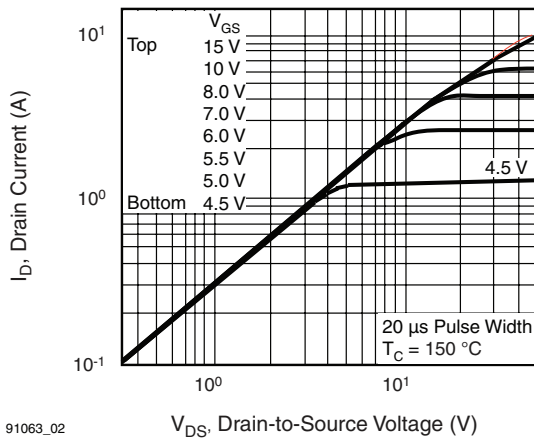
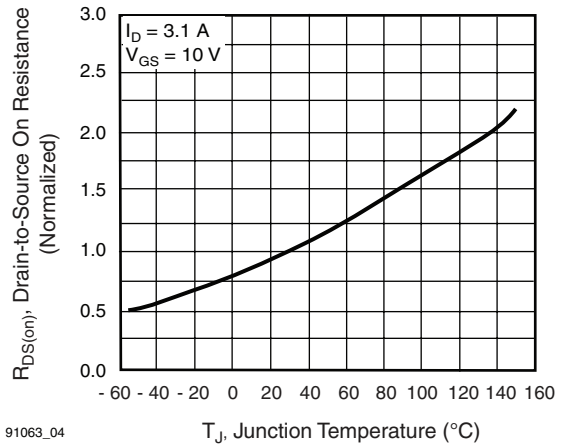
* Pb containing terminations are not RoHS compliant, exemptions may apply

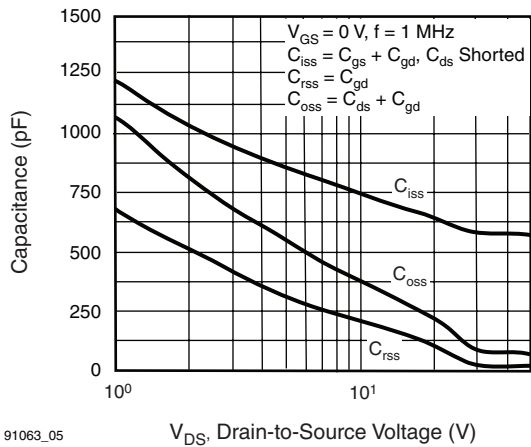
| THERMAL RESISTANCE RATINGS | | | | |
|-------------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient | R_{thJA} | - | 62 | °C/W |
| Case-to-Sink, Flat, Greased Surface | R_{thCS} | 0.50 | - | |
| Maximum Junction-to-Case (Drain) | R_{thJC} | - | 1.7 | |

| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|--------------------------------------------------------------------------|---------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------|------|------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 500 | - | - | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$ | - | 0.61 | - | V/°C |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2.0 | - | 4.0 | V |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$ | - | - | 25 | μA |
| | | $V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | - | - | 250 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 2.7\text{ A}^b$ | - | - | 1.5 | Ω |
| Forward Transconductance | g_{fs} | $V_{DS} = 50\text{ V}, I_D = 2.7\text{ A}^b$ | 2.5 | - | - | S |
| Dynamic | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz},$ see fig. 5 | - | 610 | - | pF |
| Output Capacitance | C_{oss} | | - | 160 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 68 | - | |
| Total Gate Charge | Q_g | $V_{GS} = 10\text{ V},$ $I_D = 3.1\text{ A}, V_{DS} = 400\text{ V},$ see fig. 6 and 13 ^b | - | - | 38 | nC |
| Gate-Source Charge | Q_{gs} | | - | - | 5.0 | |
| Gate-Drain Charge | Q_{gd} | | - | - | 22 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 250\text{ V}, I_D = 3.1\text{ A}$ $R_G = 12\text{ }\Omega, R_D = 79\text{ }\Omega,$ see fig. 10 ^b | - | 8.2 | - | ns |
| Rise Time | t_r | | - | 16 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 42 | - | |
| Fall Time | t_f | | - | 16 | - | |
| Internal Drain Inductance | L_D | Between lead, 6 mm (0.25") from package and center of die contact  | - | 4.5 | - | nH |
| Internal Source Inductance | L_S | | - | 7.5 | - | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | MOSFET symbol showing the integral reverse p - n junction diode  | - | - | 4.5 | A |
| Pulsed Diode Forward Current ^a | I_{SM} | | - | - | 18 | |
| Body Diode Voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}, I_S = 4.5\text{ A}, V_{GS} = 0\text{ V}^b$ | - | - | 1.6 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}, I_F = 3.1\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$ | - | 320 | 640 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | - | 1.0 | 2.0 | μC |
| Forward Turn-On Time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D) | | | | |

Notes

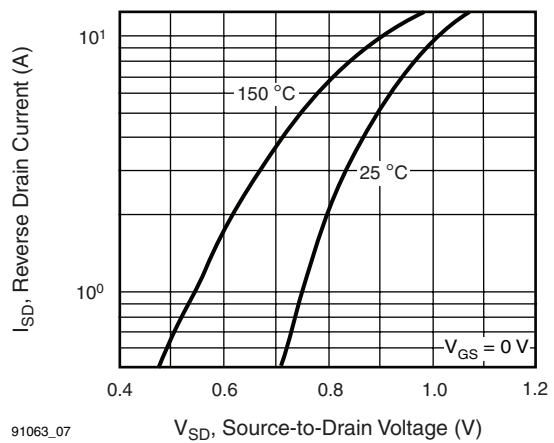
- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

Fig. 3 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

Fig. 4 - Normalized On-Resistance vs. Temperature



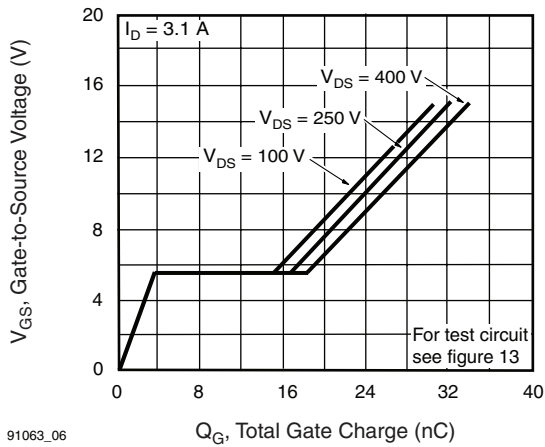
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Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



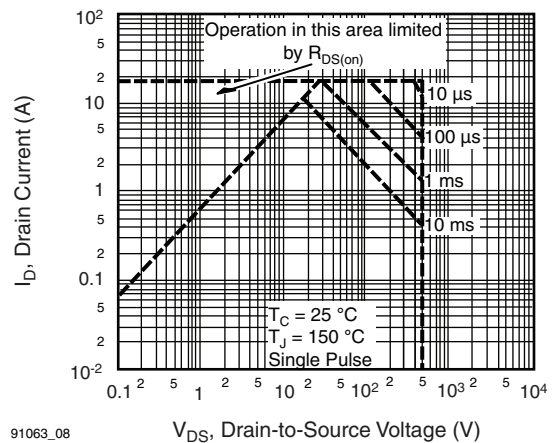
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



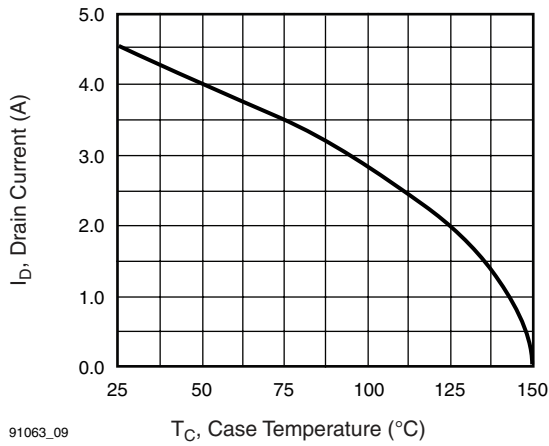
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Fig. 6 - Typical Gate Charge vs. Drain-to-Source Voltage



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Fig. 8 - Maximum Safe Operating Area



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Fig. 9 - Maximum Drain Current vs. Case Temperature

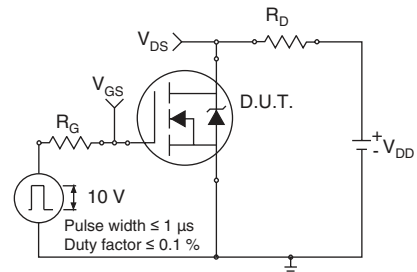


Fig. 10a - Switching Time Test Circuit

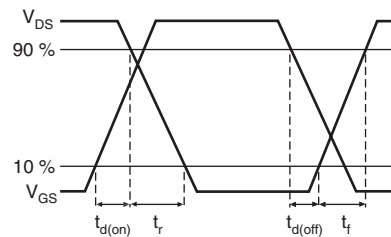
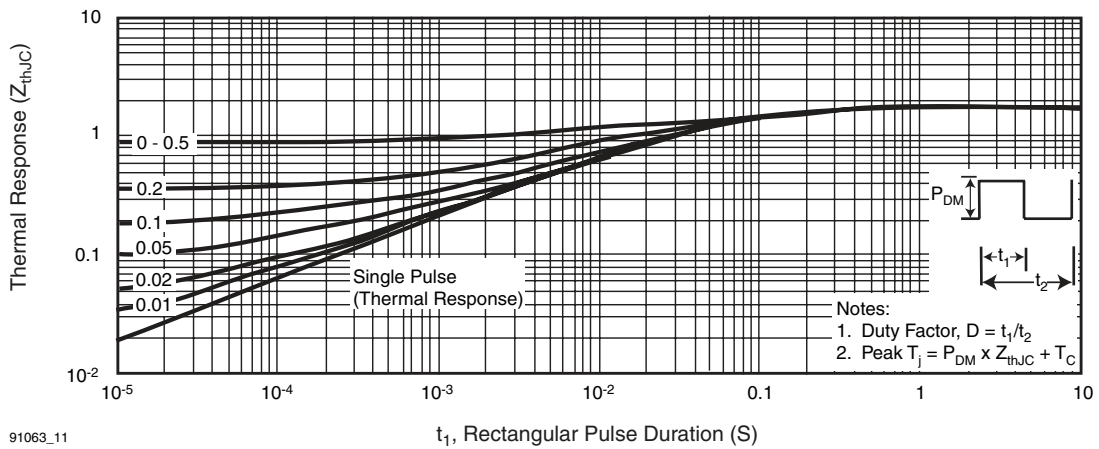


Fig. 10b - Switching Time Waveforms



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Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

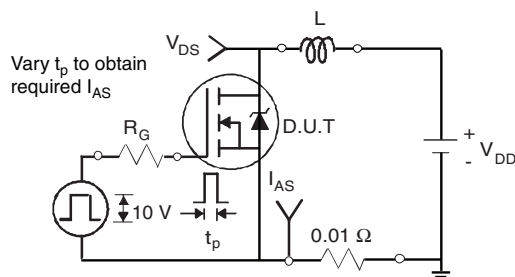


Fig. 12a - Unclamped Inductive Test Circuit

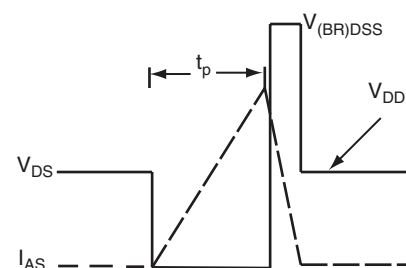


Fig. 12b - Unclamped Inductive Waveforms

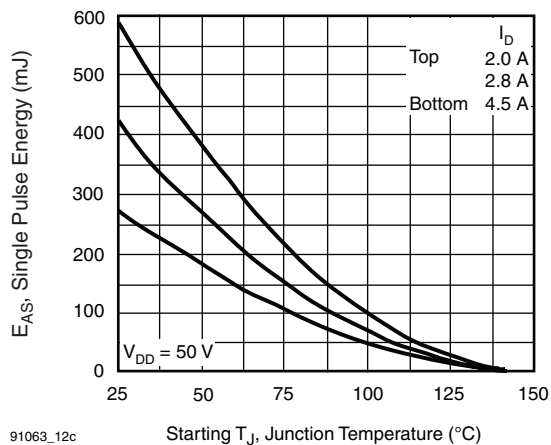


Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform

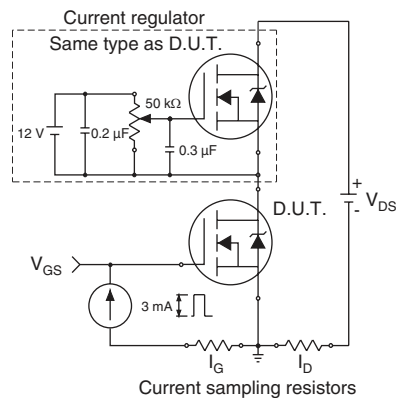
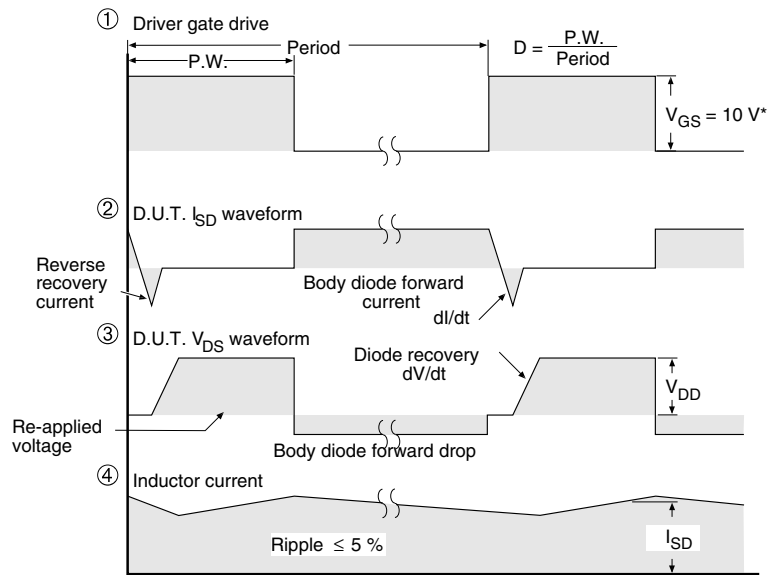
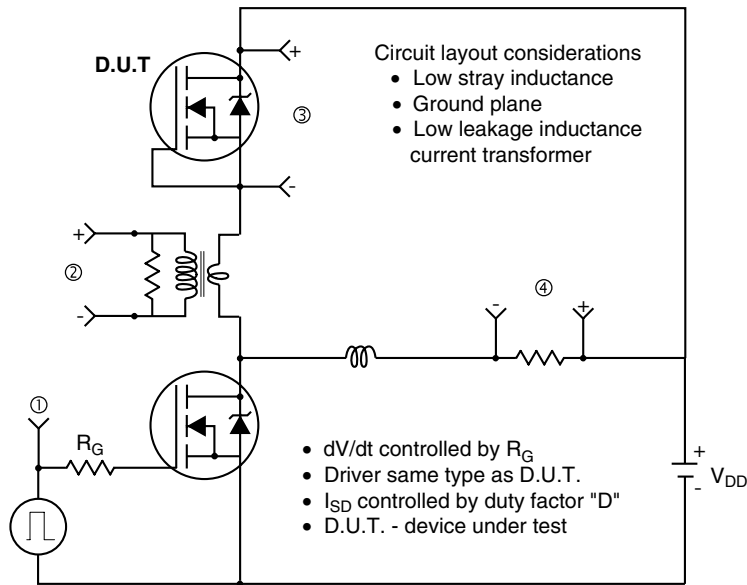


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit


* $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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